TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK3403

#### Switching Regulator Applications

- Low drain-source ON-resistance: R<sub>DS</sub> (ON) = 0.29 Ω (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 5.8 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 450 V)
- Enhancement mode:  $V_{th}$  = 3.0 to 5.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	450	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	450	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1	I <sub>D</sub>	13	А	
	Pulse (Note 1	I <sub>DP</sub>	52	A	
Drain power dissipat	ion (Tc = 25°C)	PD	100	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	350	mJ	
Avalanche current		I <sub>AR</sub>	13	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	10	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	–55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

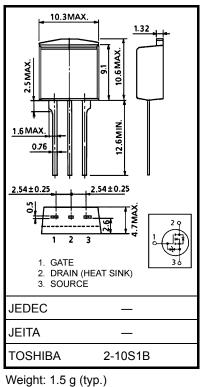
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.25	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	83.3	°C/W	

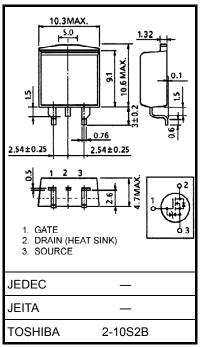
Note 1: Ensure that the channel temperature does not exceed 150°C.

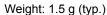
Note 2: V\_{DD} = 90 V, T\_{ch} = 25 ^{\circ}C (initial), L = 3.46 mH, R\_G = 25  $\Omega,$  I\_{AR} = 13 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.







Unit: mm

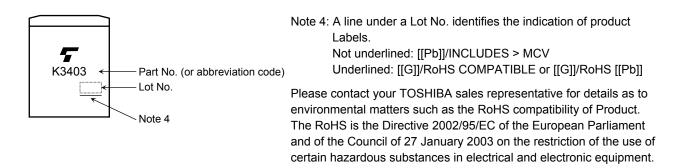
**Electrical Characteristics (Tc = 25°C)** 

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 25$ V, $V_{DS} = 0$ V			±10	μA
Gate-source brea	akdown voltage	V (BR) GSS	$I_G=\pm 10~\mu A,~V_{DS}=0~V$	±30		_	V
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 450 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			100	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	450	_	_	V
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	3.0		5.0	V
Drain-source ON	-resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	_	0.29	0.4	Ω
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$	3.0	5.8	_	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1600	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	17	_	
Output capacitance		C <sub>oss</sub>		_	220	_	
Switching time	Rise time	tr	$V_{GS}^{10 V} \downarrow I_D = 6 A$ $0 V \downarrow I_D = 6 A$ $0 V \downarrow I_D = 6 A$ $R_L =$ $33.3 \Omega$ $V_{DD} \approx 200 V$ Duty $\leq 1\%$ , $t_W = 10 \ \mu s$	_	28		
	Turn-on time	t <sub>on</sub>		_	45	_	
	Fall time	t <sub>f</sub>			10		ns
	Turn-off time	t <sub>off</sub>		_	56	_	
Total gate charge		Qg			34		nC
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 360 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 13 \text{ A}$	_	19	_	
Gate-drain charge		Q <sub>gd</sub>			15	_	

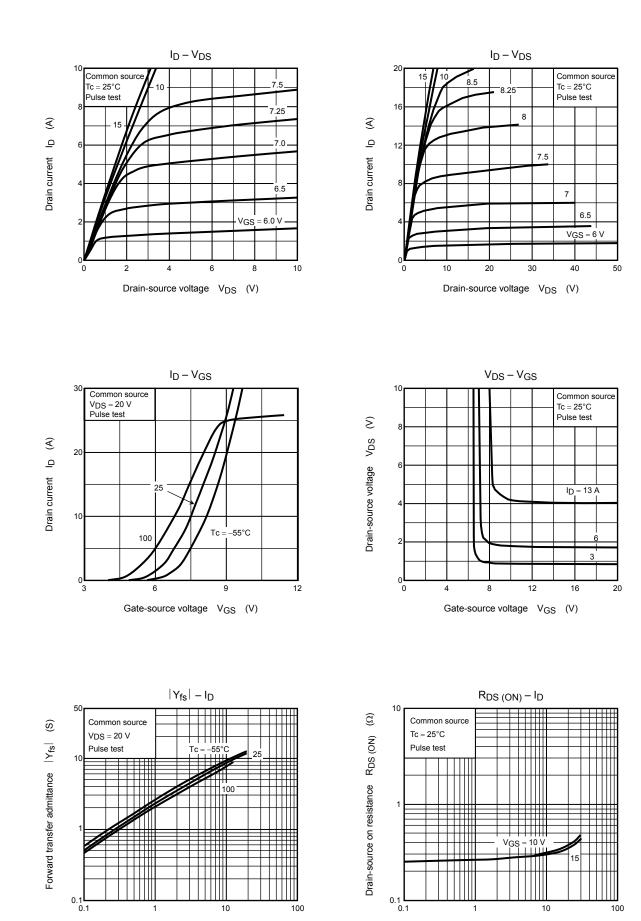
### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	13	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	52	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 13 A, V <sub>GS</sub> = 0 V,	_	300	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> /dt = 100 A/μs		3.4		μC

### Marking



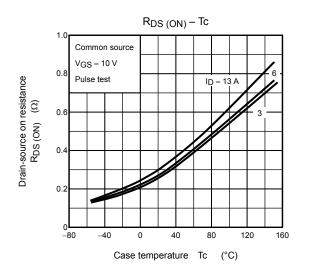
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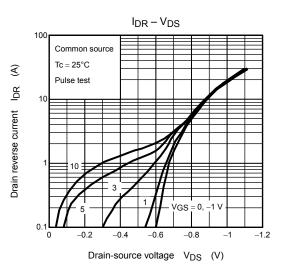


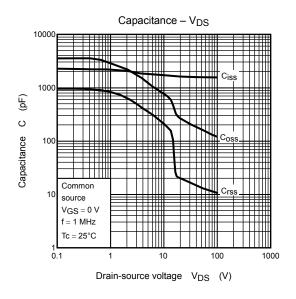
Drain current  $I_D$  (A)

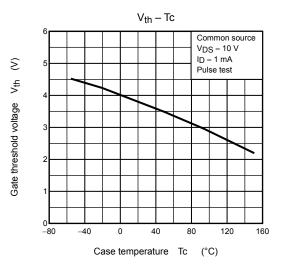
Drain current  $I_D$  (A)

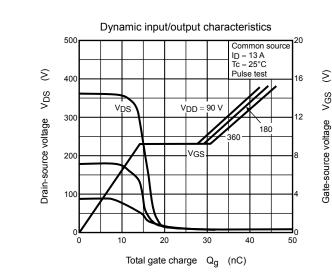
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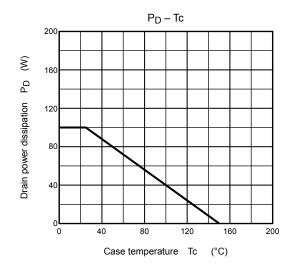


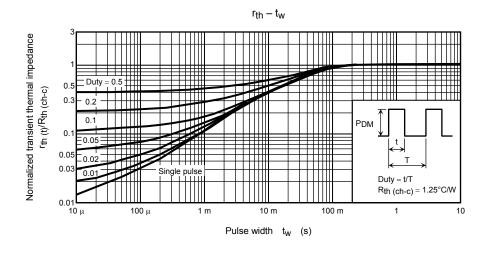


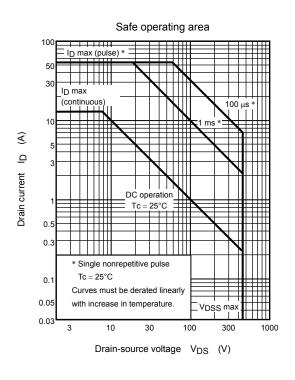


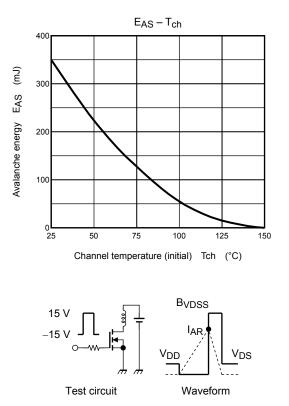


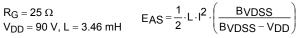












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